

University of Southern California

Viterbi School of Engineering

EE577A

VLSI System Design

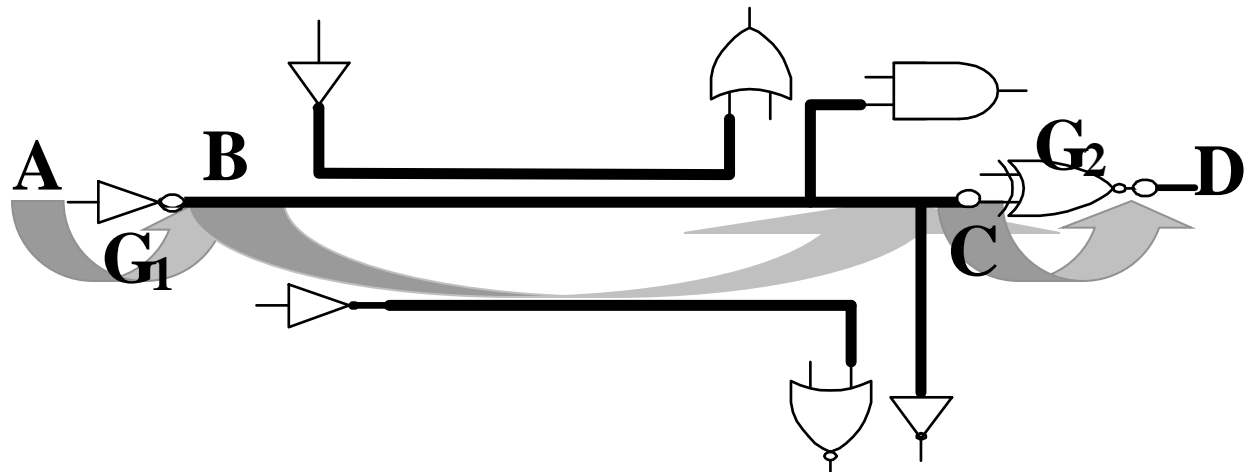
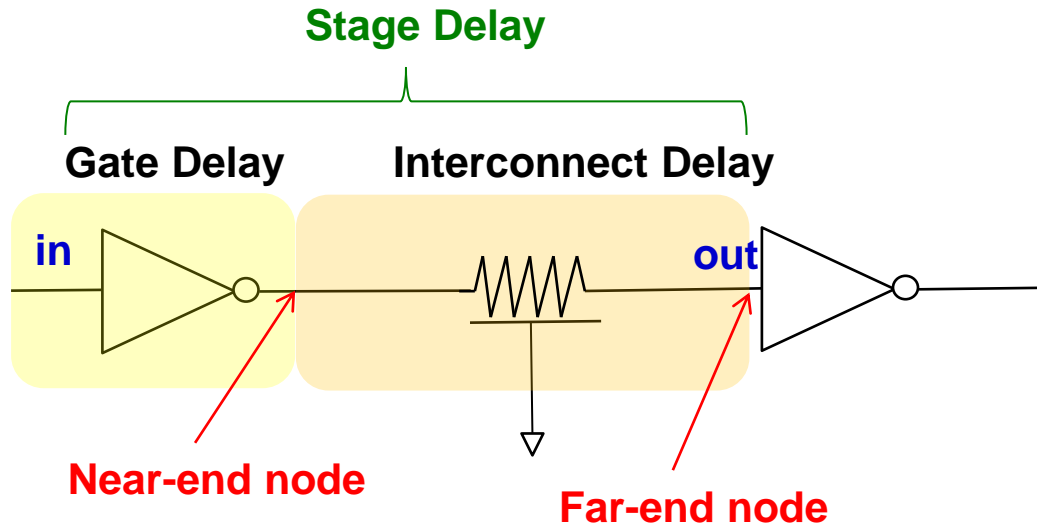
Transient Behavior of MOS Gates

**References: syllabus textbook, Professor Massoud
Pedram's slides, online resources**

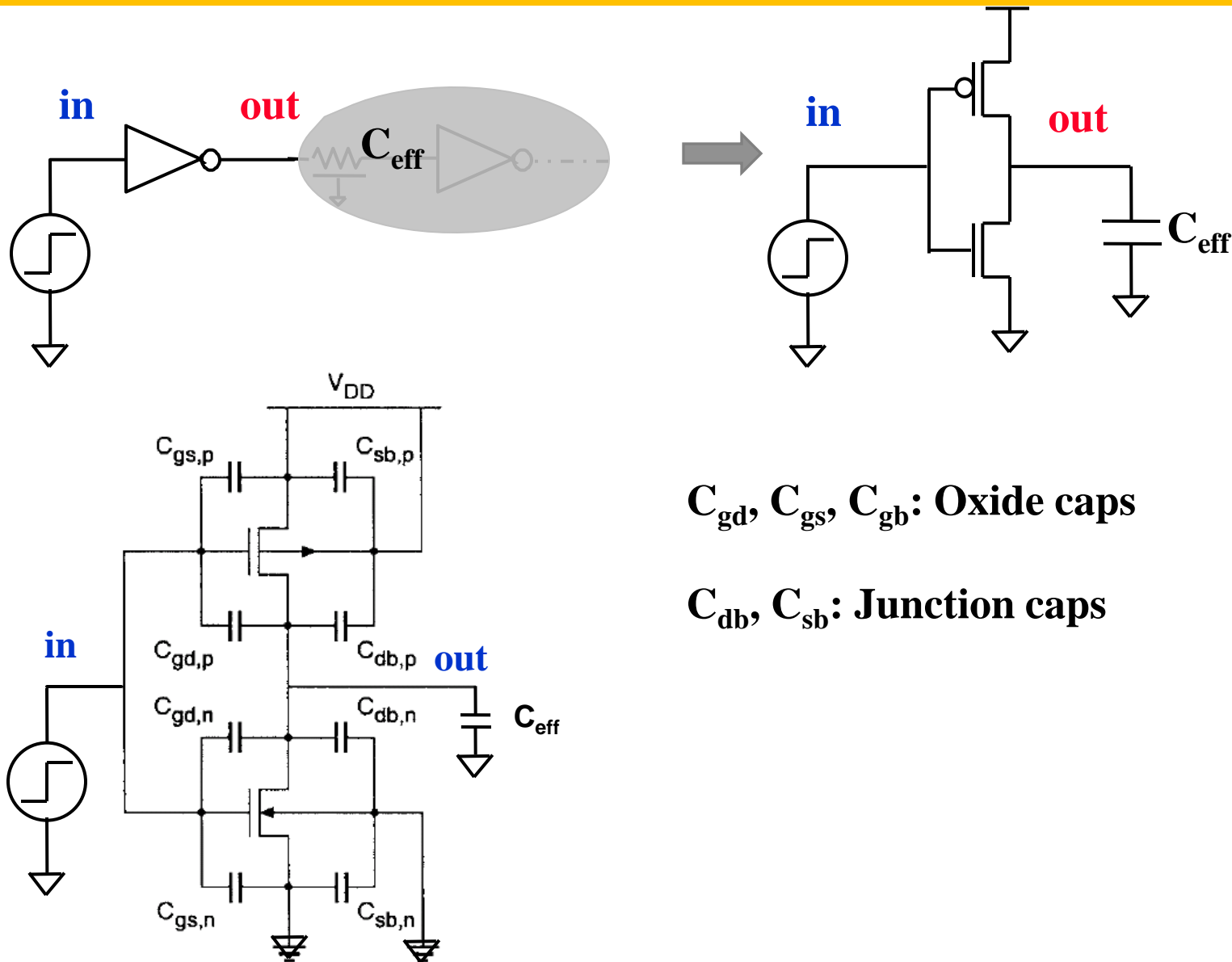
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Background



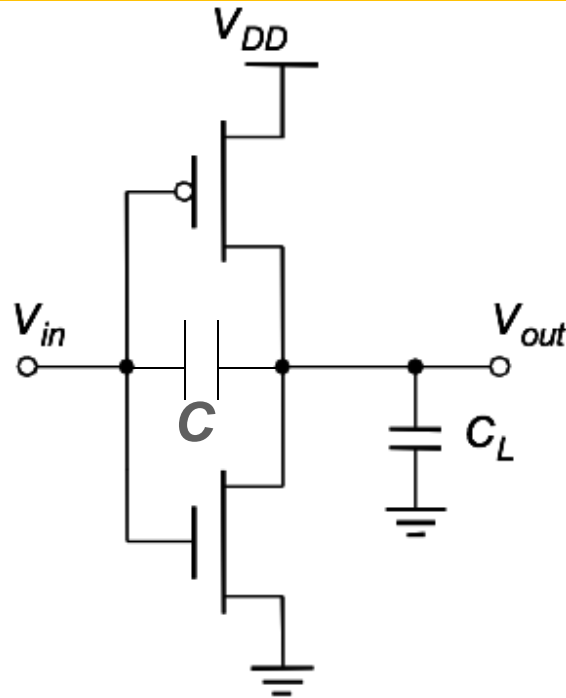
CMOS Inverter with a Single Lumped Load



C_{gd} , C_{gs} , C_{gb} : Oxide caps

C_{db} , C_{sb} : Junction caps

Miller Capacitance



$$\Delta V \uparrow \text{---} \overset{C}{\text{---}} \text{---} K\Delta V \downarrow$$

$$Q = C(\Delta V - (-K\Delta V))$$

$$= \underbrace{(K+1)C\Delta V}_{C_{eff}}$$

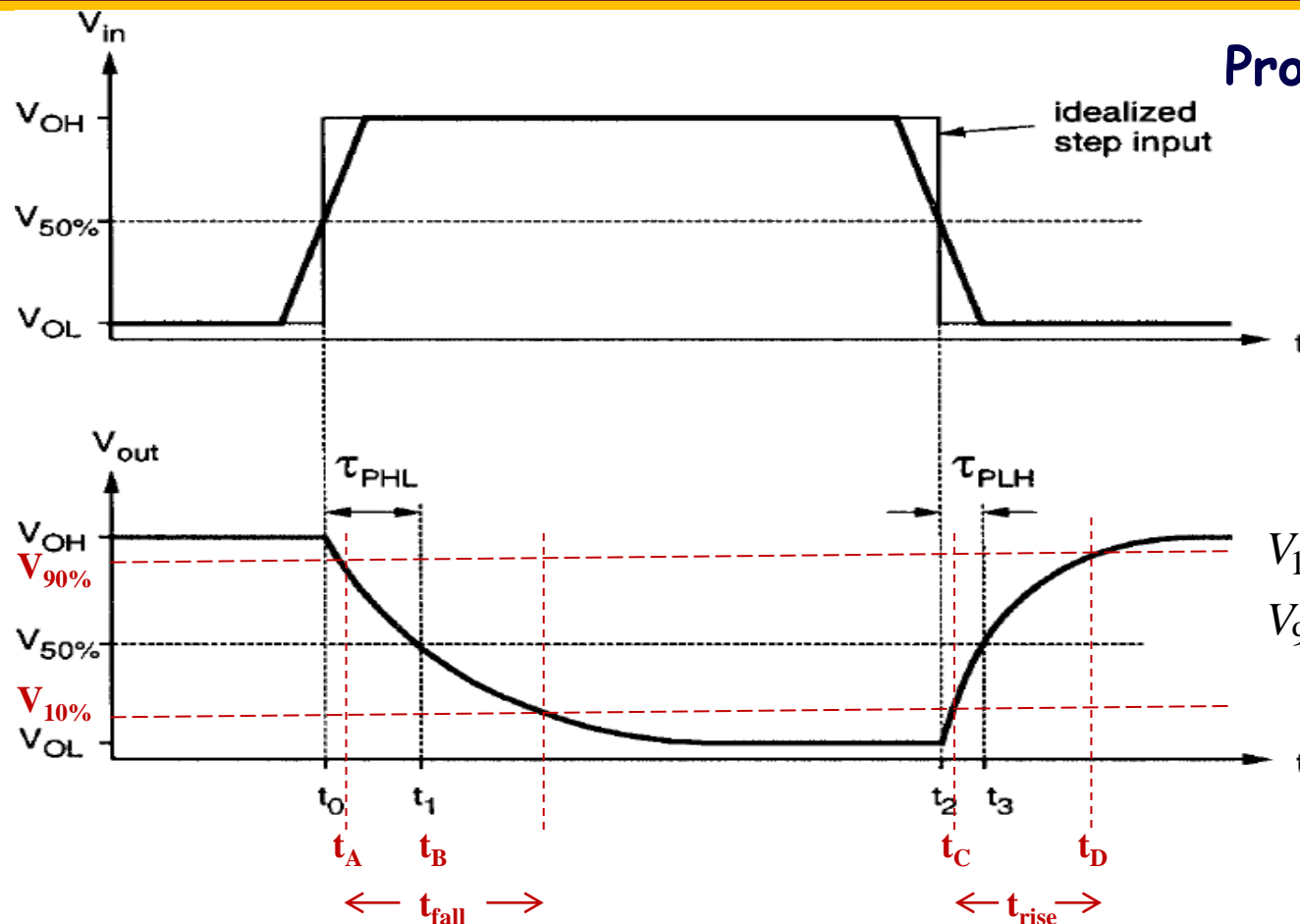
$$K=1 \rightarrow C_{eff} = 2C$$

$$C_{eff-out} = \frac{K+1}{K} C$$

$$K=1 \rightarrow C_{eff-out} = 2C$$

Effective Capacitance increases because of Miller Effect

Timing-Related Definitions



Propagation delays:

$$t_{df} \equiv \tau_{pHL} = t_1 - t_0$$

$$t_{dr} \equiv \tau_{pLH} = t_3 - t_2$$

$$V_{50\%} = \frac{1}{2}(V_{OL} + V_{OH})$$

$$V_{10\%} = V_{OL} + 0.1 \cdot (V_{OH} - V_{OL})$$

$$V_{90\%} = V_{OL} + 0.9 \cdot (V_{OH} - V_{OL})$$

Rise and Fall times aka transition times aka slews: $t_{fall} = t_B - t_A$

$$t_{rise} = t_D - t_C$$

Average Capacitance Current Method

- **Let** $I_{avg,HL}$: average current during high-to-low output transition
 $I_{avg,LH}$: average current during low-to-high output transition
- **We can write:**

$$I_{avg,HL} = \frac{1}{2} [i_c(V_{in} = V_{OH}, V_{out} = V_{OH}) + i_c(V_{in} = V_{OH}, V_{out} = V_{50\%})]$$
$$I_{avg,LH} = \frac{1}{2} [i_c(V_{in} = V_{OL}, V_{out} = V_{50\%}) + i_c(V_{in} = V_{OL}, V_{out} = V_{OL})]$$

- **Therefore,**

$$\tau_{pHL} = \frac{C_{load} \Delta V_{HL}}{I_{avg,HL}} = \frac{C_{load} (V_{OH} - V_{50\%})}{I_{avg,HL}}$$
$$\tau_{pLH} = \frac{C_{load} \Delta V_{LH}}{I_{avg,LH}} = \frac{C_{load} (V_{50\%} - V_{OL})}{I_{avg,LH}}$$

- **Similar expressions may be written for rise/fall time calculation**

Delay Calculation for Small-Geometry

- MOS Current driving capability is significantly reduced by velocity saturation:

$$I_D(sat) = W \cdot v_d(sat) \cdot C_{ox} \cdot V_{DSAT} \quad V_{DSAT} = V_{DD} - V_T$$

- Assume discharge and charge currents are approximated with the saturation current (this shows the weak dependence of t_d in low geometry)
- Better delay estimates possible with better current models such as Sakurai-Newton current model

$$t_{df} = \frac{C_{load}(V_{DD} / 2)}{W_n \cdot v_d(sat) \cdot C_{ox}(V_{DD} - V_{T,n})}$$

Delay Calculation for CMOS Gates Under Step Input: Quick Approximate Formula

- Long channel devices (quadratic current equations)

$$\tau_{pHL} = \frac{C_{load} V_{DD}}{k_n (V_{DD} - V_{tn})^2}$$

$$\tau_{pLH} = \frac{C_{load} V_{DD}}{k_p (V_{DD} - |V_{tp}|)^2}$$

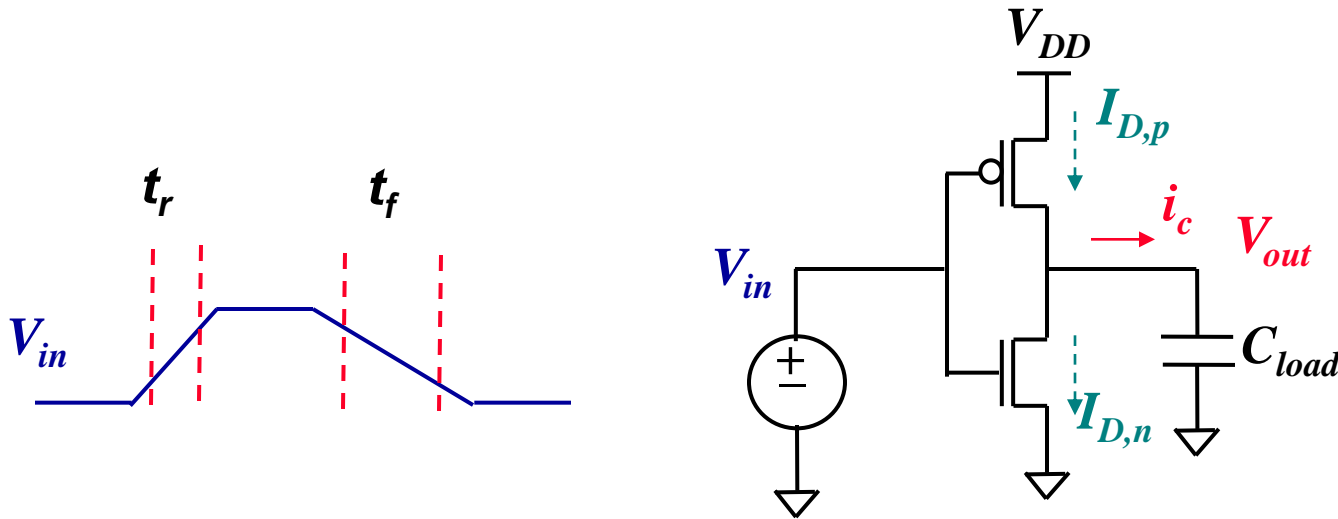
- Short channel devices (alpha-power current equations)

With $1.3 \leq \alpha \leq 1.6$,

$$\tau_{pHL} = \frac{C_{load} V_{DD}}{k_n (V_{DD} - V_{tn})^\alpha}$$

$$\tau_{pLH} = \frac{C_{load} V_{DD}}{k_p (V_{DD} - |V_{tp}|)^\alpha}$$

Gate Delay for Ramp Input



$$t_{df,ramp} = \sqrt{t_{df,step}^2 + \left(\frac{t_r}{2}\right)^2}$$

$$t_{dr,ramp} = \sqrt{t_{dr,step}^2 + \left(\frac{t_f}{2}\right)^2}$$

Fast Ramp Inputs

- Let $V_1 = V_{in} - V_{tn}$ while V_2 denote output voltage when input voltage reaches its final value
- Fast input transitions, i.e.,

$$T_{r,in} < 2\tau_{pHL,ramp} \text{ or } T_{f,in} < 2\tau_{pLH,ramp}$$

- This corresponds to the case when the driver transistor is still saturated when the input voltage ramp reaches its final value (here $V_2 \geq V_1$)

$$\begin{aligned} T_{f,out} &= 2\tau_{pHL,step} \\ T_{r,out} &= 2\tau_{pLH,step} \end{aligned}$$

$$\begin{aligned} \tau_{pHL,ramp} &= \tau_{pHL,step} + \frac{T_{r,in}}{6} \left(1 + 2 \frac{V_{tn}}{V_{DD}} \right) \\ \tau_{pLH,ramp} &= \tau_{pLH,step} + \frac{T_{f,in}}{6} \left(1 + 2 \frac{|V_{tp}|}{V_{DD}} \right) \end{aligned}$$

Slow Ramp Inputs

- Slow input transitions, i.e.,

$$T_{r,in} \geq 2\tau_{pHL,ramp} \text{ or } T_{f,in} \geq 2\tau_{pLH,ramp}$$

- Driver transistor leaves saturation while the input voltage is still ramping (here $V_2 < V_1$)
- For delay calculation there are two cases to consider: $V_2 < V_{DD}/2$ and $V_2 > V_{DD}/2$. The exact expressions are intricate and involve the *erf* and *ln* functions, respectively
- Output transition calculation requires a complicated derivation based on solving differential equations with appropriate initial values for different regions of transistor operation

Approximate Gate Delay and Transition Time Calculation for Slow Ramp Inputs

- Approximate expressions for slow input transitions, ignoring the Miller capacitance which causes over/undershoots and also causes short circuit current flow during the output transition:

- Notice that:

$$T_{r,in} = 2\tau_{pHL,ramp} \Rightarrow \tau_{pHL,ramp} = \frac{\tau_{pHL,step}}{1 - \frac{V_{tn}}{V_{DD}}}$$

$$T_{f,out} = 2\tau_{pHL,step}$$

$$\tau_{pHL,ramp} = \tau_{pHL,step} + \frac{T_{r,in}}{2} \cdot \frac{V_{tn}}{V_{DD}}$$

$$\tau_{pLH,ramp} = \tau_{pLH,step} + \frac{T_{f,in}}{2} \cdot \frac{|V_{tp}|}{V_{DD}}$$

$$T_{f,out} = 2\tau_{pHL,step} \cdot \frac{1 - \frac{V_{tn}}{V_{DD}}}{\frac{1}{2} + \frac{\tau_{pHL,ramp}}{T_{r,in}} - \frac{V_{tn}}{V_{DD}}}$$

$$T_{r,out} = 2\tau_{pLH,step} \cdot \frac{1 - \frac{|V_{tp}|}{V_{DD}}}{\frac{1}{2} + \frac{\tau_{pLH,ramp}}{T_{f,in}} - \frac{|V_{tp}|}{V_{DD}}}$$

An Example Calculation for Ramp Input

Consider an inverter driving load C_L with $t_{pHL,step}=100ps$. Calculate the gate delay and output fall time for a rising input with $T_{r,in}=25ps$. Assume $V_{tn}/V_{DD}=1/4$.

Repeat calculation for $T_{r,in}=300ps$.

Solution:

For fast ramp, $T_{r,in} = 25ps$,

$$\tau_{pHL,ramp} = \tau_{pHL,step} + \frac{T_{r,in}}{6} \left(1 + 2 \frac{V_{tn}}{V_{DD}} \right) = 100 + \frac{25}{6} \left(1 + \frac{2}{4} \right) = 106.25ps$$

$$T_{f,out} = 2 \tau_{pHL,step} = 2(100) = 200ps$$

For slow ramp, $T_{r,in} = 300ps$,

$$\tau_{pHL,ramp} = \tau_{pHL,step} + \frac{T_{r,in}}{2} \cdot \frac{V_{tn}}{V_{DD}} = 100 + \frac{300}{2} \left(\frac{1}{4} \right) = 137.5ps$$

$$T_{f,out} = 2 \tau_{pHL,step} \cdot \frac{1 - \frac{V_{tn}}{V_{DD}}}{\frac{1}{2} + \frac{\tau_{pHL,ramp}}{T_{r,in}} - \frac{V_{tn}}{V_{DD}}} = 2(100) \left(\frac{1 - \frac{1}{4}}{\frac{1}{2} + \frac{137.5}{300} - \frac{1}{4}} \right) = 200 \left(\frac{0.75}{0.708} \right) = 211.76ps$$